



High Voltage Capability

High switching speed

Features

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Pin Definition:

1. Base 2. Collector

3. Emitter

PRODUCT SUMMARY

BV _{CBO}	1050V
BV _{CEO}	550V
Ι _c	5A
V _{CE(SAT)}	0.5V @ I _C =1A, I _B =200mA

Ordering Information

Part No.	Package	Packing
TSC1203ECM RNG	TO-263	800pcs / 13" Reel

Note: "G" denote for Halogen Free Product

Absolute Maximum Rating (T_A=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Collector-Base Voltage		V _{CBO}	1050	V
Collector-Emitter Voltage		V _{CEO}	550	V
Emitter-Base Voltage		V _{EBO}	9	V
Collector Current	DC		5	٨
	Pulse(T _p <5ms)	I _C	8	A
Base Current	DC		2	٨
	Pulse(T _p <5ms)	Ι _Β	4	A
Collector Power Dissipation	T _C =25°C	P _D	36	W
Operating Junction Temperature		TJ	+150	°C
Operating Junction and Storage Temperature Range		T _{STG}	- 55 to +150	°C

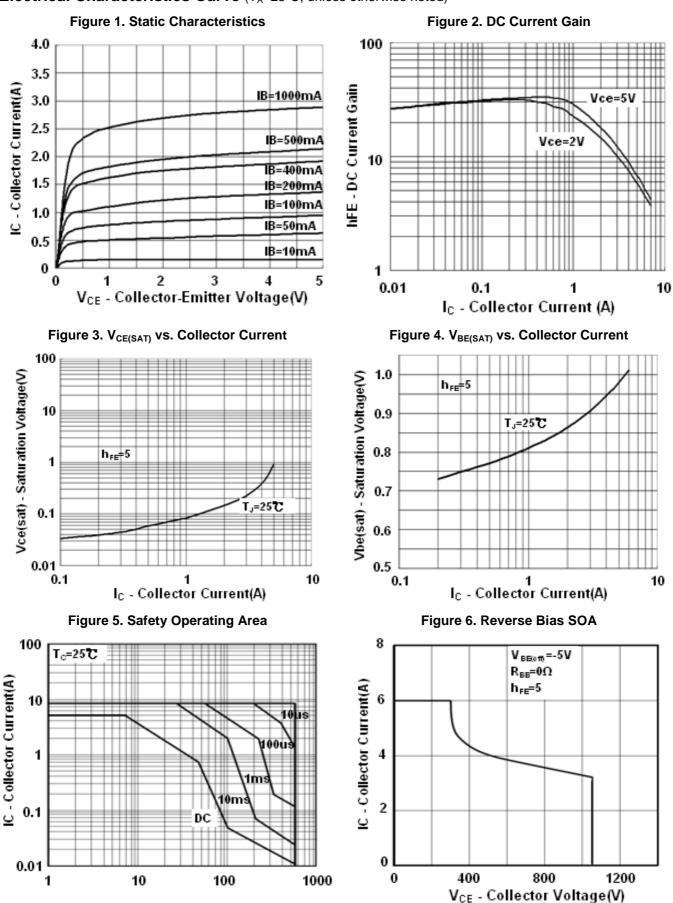
Electrical Specifications (T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	$I_{\rm C}$ =1mA, $I_{\rm B}$ =0	BV_{CBO}	1050			V
Collector-Emitter Breakdown Voltage	I _C = 5mA, I _E =0	BV_{CEO}	550			V
Emitter-Base Breakdown Voltage	$I_{E} = 10 \text{mA}, I_{C} = 0$	BV_{EBO}	9			V
Collector Cutoff Current	$V_{CE} = 1050 V, V_{BE} = 0$	I _{CES}			100	uA
Collector Cutoff Current	$V_{CE} = 550V, I_{B} = 0$	I _{CEO}			100	uA
Emitter Cutoff Current	$V_{EB} = 9V, I_{C} = 0$	I _{EBO}			10	uA
Collector-Emitter Saturation Voltage	I _C =1A, I _B =200mA	V _{CE(SAT)1}		0.12	0.5	
	I _C =2A, I _B =400mA	V _{CE(SAT)2}		0.18	0.7	V
	I _C =3A, I _B =1A	V _{CE(SAT)3}		0.22	1.5	
Page Emitter Seturation Voltage	I _C =2A, I _B =400mA	$V_{BE(SAT)1}$		0.87	1.5	V
Base-Emitter Saturation Voltage	I _C =3A, I _B =1A	V _{BE(SAT)2}		0.95	1.5	
	V_{CE} =5V, I_{C} =1mA	h _{FE} 1	10			
DC Current Transfer Patia	V_{CE} =5V, I_{C} =10mA	h _{FE} 2	10			
DC Current Transfer Ratio	V_{CE} =5V, I_C =2A	h _{FE} 3	9		28	
	$V_{CE} = 3V, I_{C} = 800 \text{mA}$	h _{FE} 4	14		32	
Resistive Load Switching Time (Ratings)						
Turn-on Time	$V_{CC} = 150V, I_C = 2A,$	t _{on}			0.5	uS
Storage Time	I _{B1} = 0.4A, I _{B2} = -0.8A,	t _s		2.5	3.5	uS
Fall Time	$t_p = 30 \text{uS}$	t _f		0.2	0.3	uS



TSC1203E High Voltage NPN Transistor

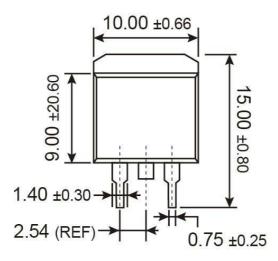
Electrical Characteristics Curve (T_A=25°C, unless otherwise noted)

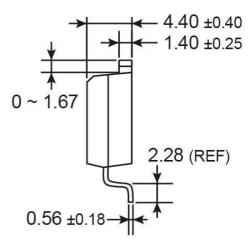




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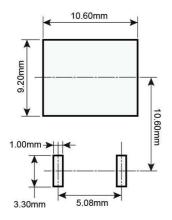
TO-263 Mechanical Drawing





Unit: Millimeters

Land Pattern Recommendation



Marking Diagram



Y	= Year Co	de				
Μ	= Month Code for Halogen Free Product					
	O =Jan	P =Feb	Q =Mar	R =Apr		
	S =May	T =Jun	U =Jul	V =Aug		
	W =Sep	X =Oct	Y =Nov	Z =Dec		
L	= Lot Cod	e (1~9. A~Z	<u>Z)</u>			



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